**Amendments to the Claims**:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A field-effect transistor comprising:

a gate electrode formed at one side of a base substrate;

a source electrode formed at the one side of the base substrate;

a drain electrode formed at the one side of the base substrate;

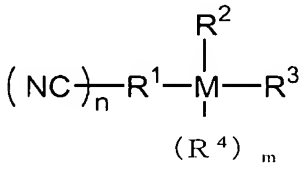
an insulation layer formed between the gate electrode and the source electrode and between the gate electrode and the drain electrode;

an organic semiconductor layer formed around the source electrode and the drain electrode; and

a reformed layer attached between the insulation layer and the organic semiconductor layer and containing a compound having the CN group in a ~~molecule.~~ molecule,

wherein the compound having the CN group in a molecule contained in or making up the reformed layer is expressed by the following chemical formula:

(Chemical formula 1)



(in the chemical formula 1, $R^1$ represents the alkylene group or the polymethylene group whose carbon number k is 1 to 20 and the alkylene group and the polymethylene group may have an ether linkage, n represents an integer of 1 to 2k, $R^2$, $R^3$, and $R^4$ each represents an organic group whose carbon number is 1 to 20 independently of each other and at least one of

$R^2$, $R^3$, and $R^4$ is the alkoxy group whose carbon number is 1 to 5 or the alkylamino group having an alkyl chain whose carbon number is 1 to 20, and M represents at least one kind of atom of Si, Ti, and Al, and when M is Si or T, m=1 and when M is Al, m=0).

2. (Currently Amended) A field-effect transistor comprising:

a gate electrode formed at one side of a base substrate;

a source electrode formed at the one side of the base substrate;

a drain electrode formed at the one side of the base substrate;

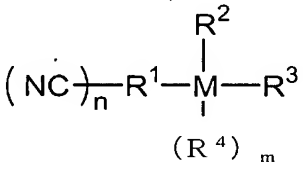
an insulation layer formed between the gate electrode and the source electrode and between the gate electrode and the drain electrode;

an organic semiconductor layer formed around the source electrode and the drain electrode; and

a reformed layer attached between the insulation layer and the organic semiconductor layer and composed of only a compound having the CN group in a ~~molecule.~~ molecule,

wherein the compound having the CN group in a molecule contained in or making up the reformed layer is expressed by the following chemical formula:

(Chemical formula 1)



(in the chemical formula 1, $R^1$ represents the alkylene group or the polymethylene group whose carbon number k is 1 to 20 and the alkylene group and the polymethylene group may have an ether linkage, n represents an integer of 1 to 2k, $R^2$, $R^3$, and $R^4$ each represents an organic group whose carbon number is 1 to 20 independently of each other and at least one of

$R^2$, $R^3$, and $R^4$ is the alkoxy group whose carbon number is 1 to 5 or the alkylamino group having an alkyl chain whose carbon number is 1 to 20, and M represents at least one kind of atom of Si, Ti, and Al, and when M is Si or T, m=1 and when M is Al, m=0).

3. (Canceled)

4. (Previously Presented) The field-effect transistor according to claim 1, wherein the compound having the CN group in a molecule contained in or making up the reformed layer is 2-cyanoethyltriethoxy silane.

5. (Original) The field-effect transistor according to claim 1, wherein the concentration of the compound having the CN group in a molecule contained in the reformed layer is less than 50 mass%.

6. (Original) The field-effect transistor according to claim 1, wherein the thickness of the reformed layer is 0.5 to 500 nm.

7. (Previously Presented) The field-effect transistor according to claim 1, wherein $C_{min}$ representing the minimum value of the electrostatic capacitance in the electrostatic capacitance-gate voltage characteristic of the field-effect transistor and $C_{max}$ representing the maximum value of the electrostatic capacitance in the electrostatic capacitance-gate voltage characteristic of the field-effect transistor satisfy the following expression:

$$C_{max} \leq C_{min} \times 2.$$

8. (Previously Presented) The field-effect transistor according to claim 1, wherein the curve of the rate of change of the drain current obtained from the drain current-time characteristic has a local extreme value, the first derivative is substantially positive, or the rate of change exceeds 1 when 10 seconds elapse after the gate voltage is applied.

9. (Currently Amended) The field-effect transistor according to claim 2, wherein ~~the~~ an hydroxyl group is introduced to ~~the~~ a surface or ~~the~~ a surface layer of the insulation layer.

10. (Canceled)

11. (Previously Presented) The field-effect transistor according to claim 2, wherein the compound having the CN group in a molecule contained in or making up the reformed layer is 2-cyanoethyltriethoxy silane.

12. (Previously Presented) The field-effect transistor according to claim 2, wherein $C_{min}$ representing the minimum value of the electrostatic capacitance in the electrostatic capacitance-gate voltage characteristic of the field-effect transistor and $C_{max}$ representing the maximum value of the electrostatic capacitance in the electrostatic capacitance-gate voltage characteristic of the field-effect transistor satisfy the following expression:

$$C_{max} \leq C_{min} \times 2.$$

13. (Previously Presented) The field-effect transistor according to claim 2, wherein the curve of the rate of change of the drain current obtained from the drain current-time characteristic has a local extreme value, the first derivative is substantially positive, or the rate of change exceeds 1 when 10 seconds elapse after the gate voltage is applied.